



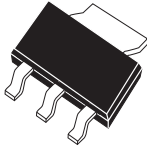
**CZS5064**

**SILICON CONTROLLED RECTIFIER**

**Central**<sup>TM</sup>  
Semiconductor Corp.

**DESCRIPTION**

The CENTRAL SEMICONDUCTOR CZS5064 type is an epoxy molded PNP Silicon Controlled Rectifier manufactured in an epoxy molded surface mount package, designed for control systems and sensing circuit applications.



**SOT-223 CASE**

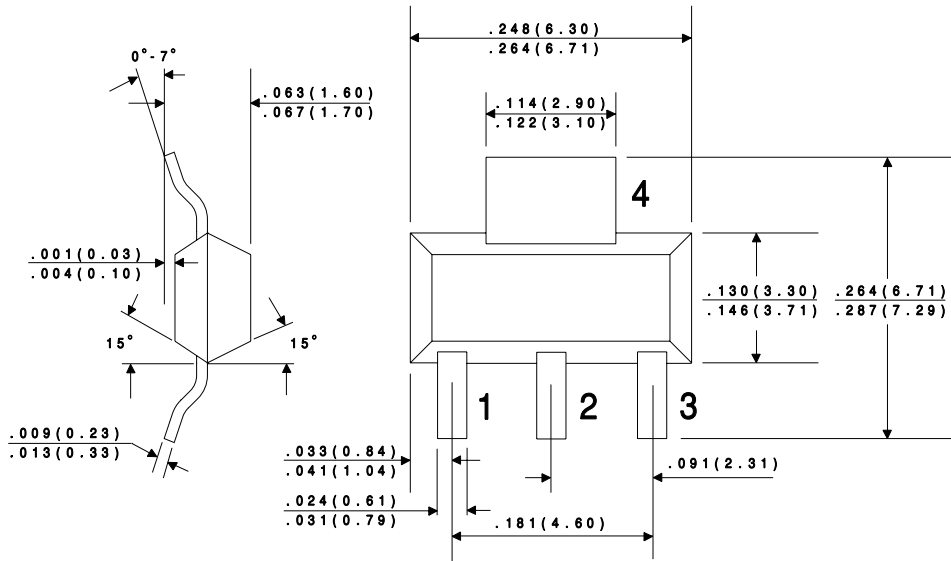
**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Off-State Voltage	$V_{DRM}$	400	V
Peak Repetitive Reverse Voltage	$V_{RRM}$	400	V
RMS On-State Current	$I_T(\text{RMS})$	0.8	A
Average On-State Current ( $T_C=67^{\circ}\text{C}$ )	$I_T(\text{AV})$	0.51	A
Operating Junction Temperature	$T_J$	-40 to +125	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-40 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JA}$	150	$^{\circ}\text{C}/\text{W}$
Thermal Resistance	$\theta_{JC}$	25	$^{\circ}\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{DRM}$	$V_D=400\text{V}, R_{GK}=1\text{K}\Omega, T_C=125^{\circ}\text{C}$		50	$\mu\text{A}$
$I_{RRM}$	$V_D=400\text{V}, R_{GK}=1\text{K}\Omega, T_C=125^{\circ}\text{C}$		50	$\mu\text{A}$
$V_T$	$I_T=1.2\text{A}$		1.7	V
$I_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega$		200	$\mu\text{A}$
$V_{GT}$	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega$		0.8	V
$V_{GD}$	$V_D=400\text{V}, R_L=100\Omega, T_C=125^{\circ}\text{C}$	0.1		V
$I_H$	$V_D=7.0, R_{GK}=1\text{K}\Omega$		5.0	mA
$t_{ON}$	$V_D=400\text{V}, I_{GT}=1.0\text{mA}, I_F=1.0\text{A}, R_{GK}=1.0\Omega, di/dt=6.0\text{A}/\mu\text{s}$		2.8 TYP	$\mu\text{s}$

All dimensions in inches (mm).



LEAD CODE:

- 1) CATHODE
- 2) ANODE
- 3) GATE
- 4) ANODE